

-30V P-Channel Enhancement Mode MOSFET

Description

The SX4435B uses advanced trench technology to provide excellent Rds(ON), low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

 $V_{DS} = -30V I_{D} = -9.3A$

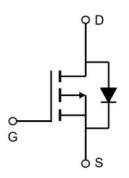
 $R_{DS(ON)}$ <20m Ω @ V_{GS}=-10V

Application

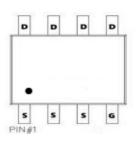
Lithium battery protection

Wireless impact

Mobile phone fast charging







Absolute Maximum Ratings (TC=25°Cunless otherwise noted)

Symbol	Parameter	Rating	Units
VDS	Drain-Source Voltage	-30	V
VGS	Gate-Source Voltage	±20	V
l o@Ta=25°C	Continuous Drain Current, V _{GS} @ -10V¹	-9.3	Α
lo@Ta=70°C	Continuous Drain Current, V _{GS} @ -10V ¹	-7.0	Α
IDM	Pulsed Drain Current ²	-50	А
Pb@Ta=25°C	Total Power Dissipation ⁴	3.1	W
Pb@Ta=70°C	Total Power Dissipation ⁴	2	W
TSTG	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C
ReJA	Thermal Resistance Junction-Ambient ¹(t≦ 10s)	33.8	°C/W
R₀JC	Thermal Resistance Junction-Case ¹	24	°C/W





Electrical Characteristics (T_J=25℃, unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V(BR)DSS	Drain-Source Breakdown Voltage	Vgs=0V, Ip= -250µA	-30	-33	-	V
IDSS	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} =0V,	-	-	-1	μA
IGSS	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
VGS(th)	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D = -250µA	-1.2	-1.5	-2.5	V
DDG()	Static Drain-Source on-Resistance note3	Vgs= -10V, ID= -10A	-	16	20	mΩ
RDS(on)		V _G S= -4.5V, I _D = -5A	-	25	30	
Ciss	Input Capacitance		-	1550	-	pF
Coss	Output Capacitance	V _{DS} = -15V, V _{GS} =0V, f=1.0MHz	-	327	-	pF
Crss	Reverse Transfer Capacitance	1-1.0IVII 12	_	278	_	pF
Qg	Total Gate Charge		-	30	-	nC
Qgs	Gate-Source Charge	V _{DS} = -15V, I _D = -9.1A,	-	5.3	-	nC
Qgd	Gate-Drain("Miller") Charge	V _G s= -10V	_	7.6	_	nC
td(on)	Turn-on Delay Time		-	14	-	ns
tr	Turn-on Rise Time	VDD= -15V, ID= -6A,	-	20	-	ns
td(off)	Turn-off Delay Time	V _G S= -10V, R _G EN=2.5Ω	-	95	-	ns
t _f	Turn-off Fall Time		-	65	-	ns
IS	Maximum Continuous Drain to Source Diode Forward Current		-	-	-10	Α
ISM	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	Α
VSD	Drain to Source Diode Forward Voltage	Vgs=0V, Is= -11A	-	-0.8	-1.2	V

Note:

- 1 . The data tested by surface mounted on a 1 inch 2 FR-4 board with 2OZ copper.
- 2 . The data tested by pulsed , pulse width ≤ 300 us , duty cycle $\leq 2\%$
- 3 The EAS data shows Max. rating . The test condition is VDD=-25V,VGS=-10V,L=0.1mH,IAS=-5A
- 5. The data is theoretically the same as ID and IDM, in real applications, should be limited by total power dissipation.

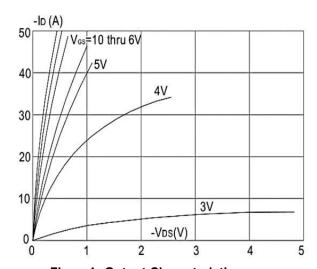
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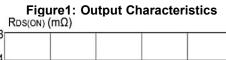
www.sxsemi.com





Typical Characteristics





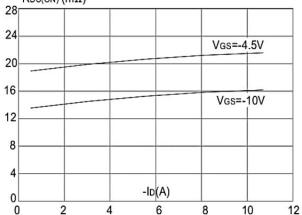


Figure 3:On-resistance vs Drain Current

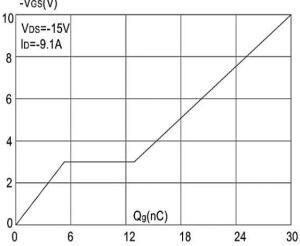
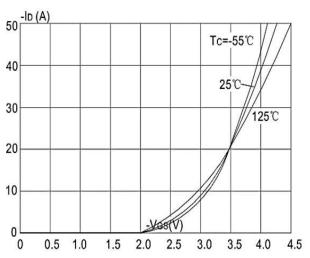


Figure 5: Gate Charge Characteristics



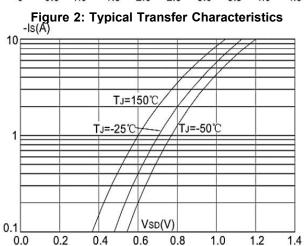


Figure 4: Body Diode Characteristics

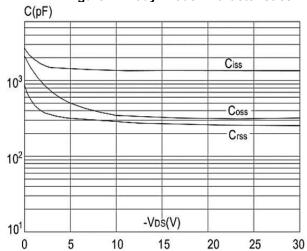
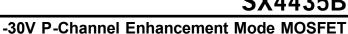


Figure 6: Capacitance Characteristics



Typical Characteristics

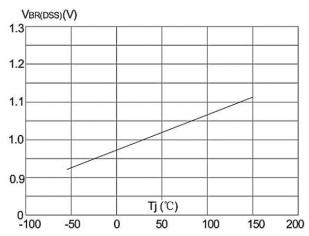


Figure 7: Normalized Breakdown Voltage vs. **Junction Temperature**

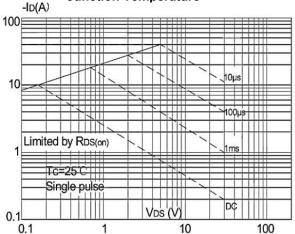


Figure 9: Maximum Safe Operating Area

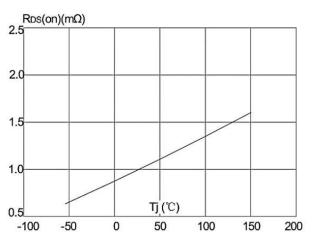


Figure 8: Normalized on Resistance vs. **Junction Temperature**

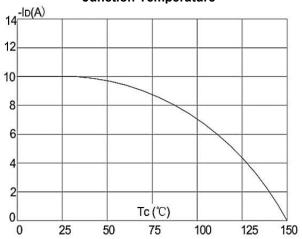


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

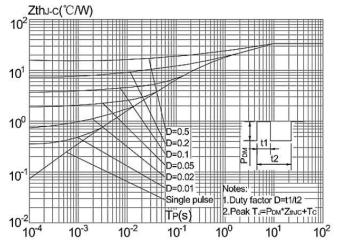
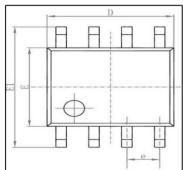


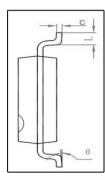
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

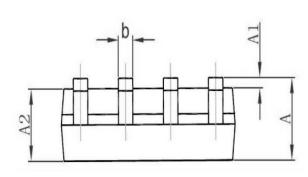


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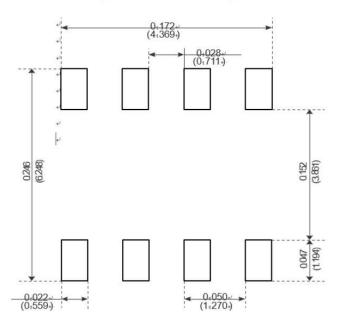
Package Mechanical Data-SOP-8







Cl 1	Dimensions In	n Millimeters	Dimensions	In Inches
Symbol	Min	Max	Min	Max
Α	1. 350	1. 750	0. 053	0.069
A1	0. 100	0. 250	0. 004	0. 010
A2	1. 350	1. 550	0. 053	0.061
b	0. 330	0. 510	0. 013	0. 020
С	0. 170	0. 250	0.006	0. 010
D	4. 700	5. 100	0. 185	0. 200
E	3.800	4. 000	0. 150	0. 157
E1	5. 800	6. 200	0. 228	0. 244
е	1. 270	(BSC)	0.050	(BSC)
L	0. 400	1. 270	0. 016	0.050
θ	0°	8°	0°	8°



Recommended Minimum Pads

Package Marking and Ordering Information

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Product ID	Pack	Marking	Qty(PCS)
TAPING	SOP-8		3000

5